

Fast Recovery Diodes (Stud Version), 40 A, 70 A, 85 A



DO-203AB (DO-5)

FEATURES

- Short reverse recovery time
- Low stored charge
- Wide current range
- Excellent surge capabilities
- Stud cathode and stud anode versions
- Types up to 100 V_{RRM}
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC power supplies
- Inverters
- Converters
- Choppers
- Ultrasonic systems
- Freewheeling diodes

PRODUCT SUMMARY

I _{F(AV)}	40 A, 70 A, 85 A
Package	DO-203AB (DO-5)
Circuit configuration	Single diode

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	40HFL	70HFL	85HFL	UNITS
I _{F(AV)}		40	70	85	A
	T _C maximum	85	85	85	°C
I _{FSM}	50 Hz	400	700	1100	A
	60 Hz	420	730	1151	
I ² t	50 Hz	800	2450	6050	A ² s
	60 Hz	730	2240	5523	
I ² √t		11 300	34 650	85 560	I ² √s
V _{RRM}	Range	100 to 1000	100 to 1000	100 to 1000	V
t _{rr}		See Recovery Characteristics table	See Recovery Characteristics table	See Recovery Characteristics table	ns
T _J	Range	-40 to 125	-40 to 125	-40 to 125	°C



ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER ⁽¹⁾	V_{RRM} , MAXIMUM PEAK REPETITIVE REVERSE VOLTAGE $T_J = -40\text{ }^{\circ}\text{C TO }125\text{ }^{\circ}\text{C}$ V	V_{RSM} , MAXIMUM PEAK NON-REPETITIVE REVERSE VOLTAGE $T_J = 25\text{ }^{\circ}\text{C TO }125\text{ }^{\circ}\text{C}$ V	I_{FM} , MAXIMUM PEAK REVERSE CURRENT AT RATED V_{RRM} mA	
			$T_J = 25\text{ }^{\circ}\text{C}$	$T_J = 125\text{ }^{\circ}\text{C}$
VS-40HFL10S02, VS-40HFL10S05	100	150	0.1	10
VS-40HFL20S02, VS-40HFL20S05	200	300		
VS-40HFL40S02, VS-40HFL40S05	400	500		
VS-40HFL60S02, VS-40HFL60S05	600	700		
VS-40HFL80S05	800	900		
VS-40HFL100S05	1000	1100		
VS-70HFL10S02, VS-70HFL10S05	100	150	0.1	15
VS-70HFL20S02, VS-70HFL20S05	200	300		
VS-70HFL40S02, VS-70HFL40S05	400	500		
VS-70HFL60S02, VS-70HFL60S05	600	700		
VS-70HFL80S05	800	900		
VS-70HFL100S05	1000	1100		
VS-85HFL10S02, VS-85HFL10S05	100	150	0.1	20
VS-85HFL20S02, VS-85HFL20S05	200	300		
VS-85HFL40S02, VS-85HFL40S05	400	500		
VS-85HFL60S02, VS-85HFL60S05	600	700		
VS-85HFL80S05	800	900		
VS-85HFL100S05	1000	1100		

Note

⁽¹⁾ Types listed are cathode case, for anode case add "R" to code, i.e. 40HFLR20S02, 85HFLR100S05 etc.

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS	40HFL	70HFL	85HFL	UNITS
Maximum average forward current at maximum case temperature	$I_{F(AV)}$	180° conduction, half sine wave	40	70	85	A
			75			°C
Maximum RMS forward current	$I_{F(RMS)}$		63	110	134	A
Maximum peak repetitive forward current	I_{FRM}	Sinusoidal half wave, 30° conduction	220	380	470	A
Maximum peak, one-cycle non-repetitive forward current	I_{FSM}	t = 10 ms	400	700	1100	A
		t = 8.3 ms	420	730	1151	
		t = 10 ms	475	830	1308	
		t = 8.3 ms	500	870	1369	
Maximum I^2t for fusing	I^2t	t = 10 ms	800	2450	6050	A ² s
		t = 8.3 ms	730	2240	5523	
		t = 10 ms	1130	3460	8556	
		t = 8.3 ms	1030	3160	7810	
Maximum $I^2\sqrt{t}$ for fusing ⁽¹⁾	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied	11 300	34 650	85 560	A ² √s
Maximum value of threshold voltage	$V_{F(TO)}$	$T_J = 125\text{ }^{\circ}\text{C}$	1.081	1.085	1.128	V
Maximum value of forward slope resistance	r_F		6.33	3.40	2.11	mΩ
Maximum forward voltage drop	V_{FM}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_{FM} = \pi \times I_{F(AV)}$	1.95	1.85	1.75	V

Note

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

RECOVERY CHARACTERISTICS

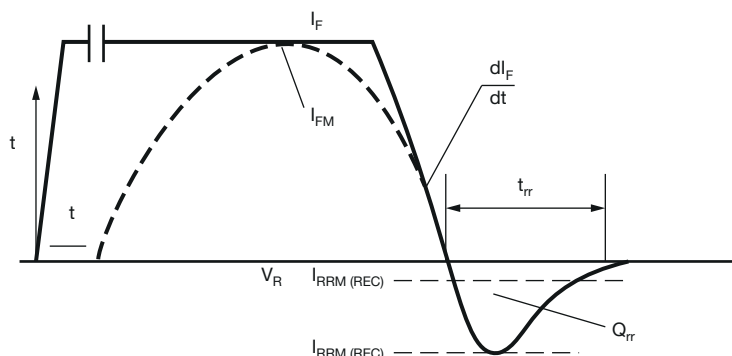
PARAMETER	SYMBOL	TEST CONDITIONS	40HFL...		70HFL...		85HFL...		UNITS
			S02	S05	S02	S05	S02	S05	
Typical reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 1\text{ A}$ to $V_R = 30\text{ V}$, $di_F/dt = 100\text{ A}/\mu\text{s}$	70	180	60	150	50	120	ns
		$T_J = 25\text{ }^{\circ}\text{C}$, $-di_F/dt = 25\text{ A}/\mu\text{s}$, $I_{FM} = \pi \times \text{rated } I_{F(AV)}$	200	500	200	500	200	500	
Typical reverse recovered charge	Q_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 1\text{ A}$ to $V_R = 30\text{ V}$, $di_F/dt = 100\text{ A}/\mu\text{s}$	160	750	90	500	70	340	nC
		$T_J = 25\text{ }^{\circ}\text{C}$, $-di_F/dt = 25\text{ A}/\mu\text{s}$, $I_{FM} = \pi \times \text{rated } I_{F(AV)}$	240	1300	240	1300	240	1300	

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	40HFL	70HFL	85HFL	UNITS
Junction operating temperature range	T _J		- 40 to 125			°C
Storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.60	0.36	0.30	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25			
Maximum allowable mounting torque (+ 0 %, - 10 %)		Not lubricated thread, tightening on nut ⁽¹⁾	3.4 (30)			N · m (lbf · in)
		Lubricated thread, tightening on nut ⁽¹⁾	2.3 (20)			
		Not lubricated thread, tightening on hexagon ⁽²⁾	4.2 (37)			
		Lubricated thread, tightening on hexagon ⁽²⁾	3.2 (28)			
Approximate weight			25			
			0.88			
Case style		JEDEC	DO-203AB (DO-5)			

Notes

- (1) Recommended for pass-through holes
(2) Recommended for holed threaded heatsinks



I_F , I_{FM} - Peak forward current prior to commutation
 $-di_F/dt$ - Rate of fall forward current
 $I_{RRM(REC)}$ - Peak reverse recovery current
 t_{rr} - Reverse recovery time
 Q_{rr} - Reverse recovered charge

Fig. 1 - Reverse Recovery Time Test Waveform

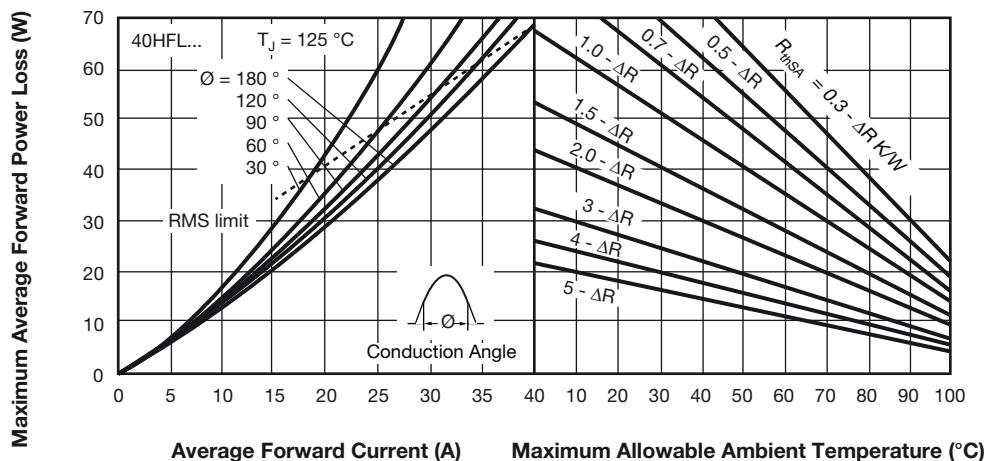


Fig. 2 - Current Rating Nomogram (Sinusoidal Waveforms), 40HFL Series

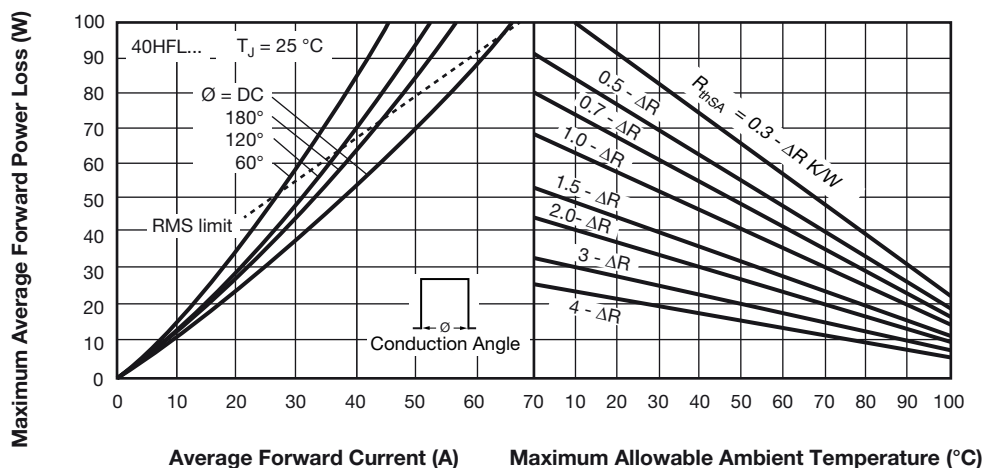


Fig. 3 - Current Rating Nomogram (Rectangular Waveforms), 40HFL Series

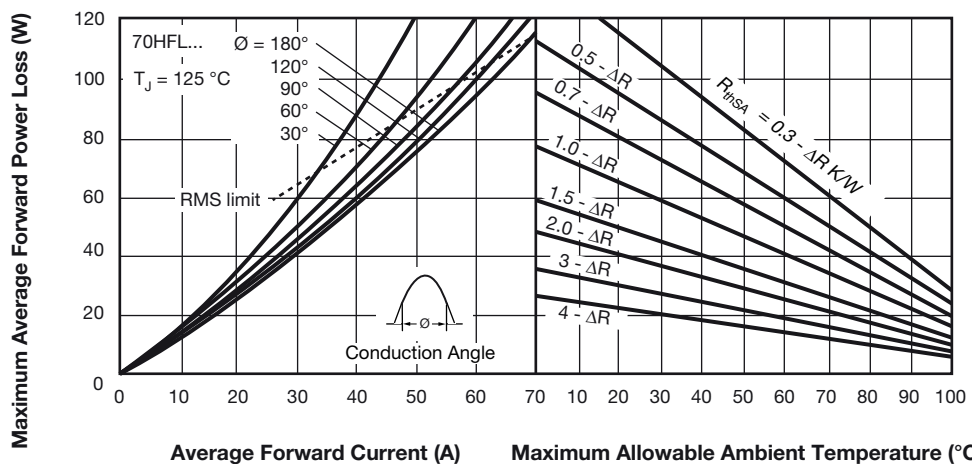


Fig. 4 - Current Rating Nomogram (Sinusoidal Waveforms), 70HFL Series

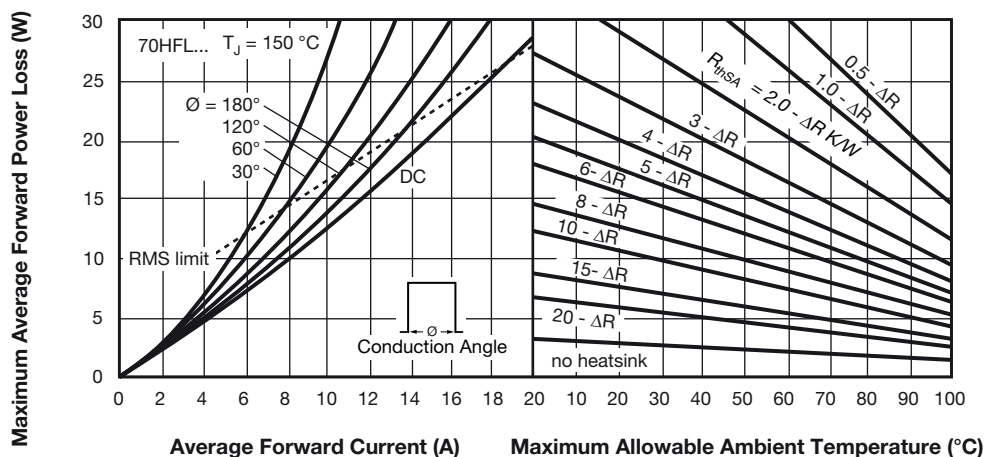


Fig. 5 - Current Rating Nomogram (Rectangular Waveforms), 70HFL Series

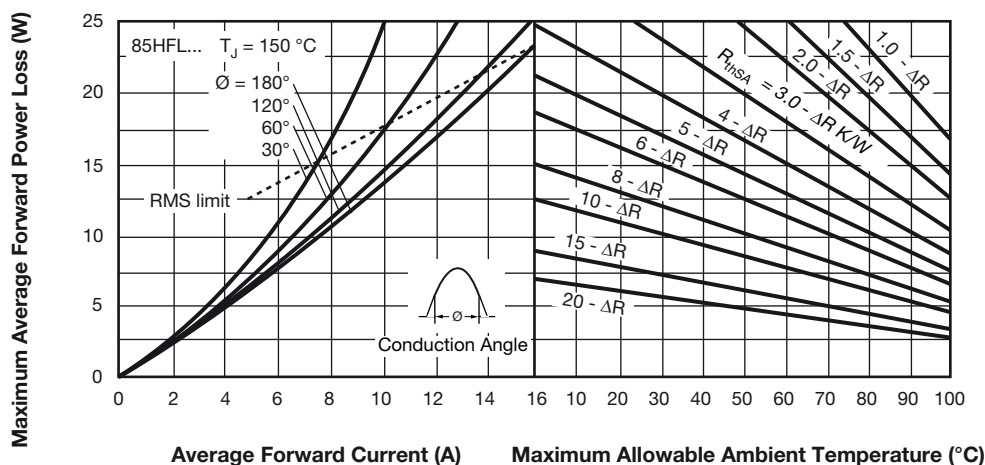


Fig. 6 - Current Rating Nomogram (Sinusoidal Waveforms), 85HFL Series

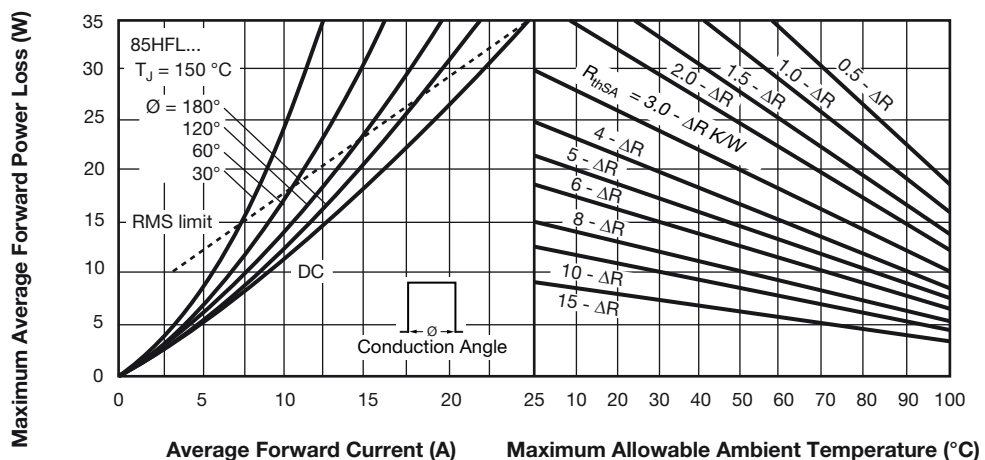


Fig. 7 - Current Rating Nomogram (Rectangular Waveforms), 85HFL Series

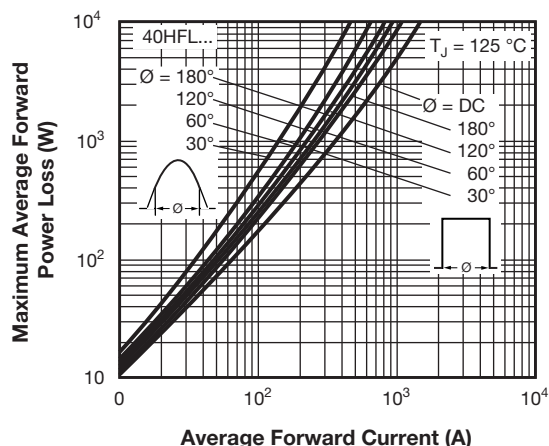


Fig. 8 - Maximum High Level Forward Power Loss vs. Average Forward Current, 40HFL Series

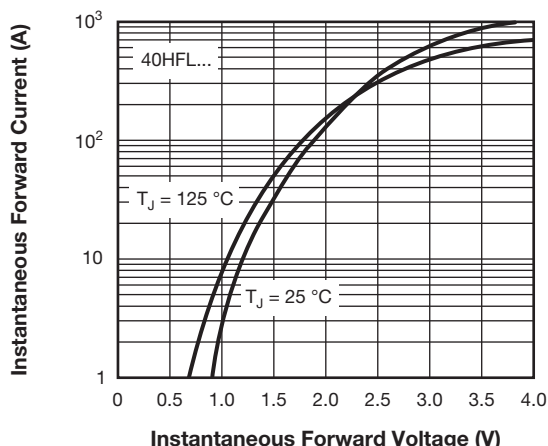


Fig. 11 - Maximum Forward Voltage vs. Forward Current, 40HFL Series

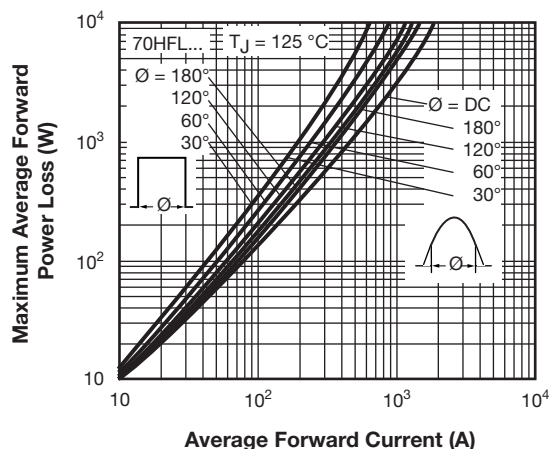


Fig. 9 - Maximum High Level Forward Power Loss vs. Average Forward Current, 70HFL Series

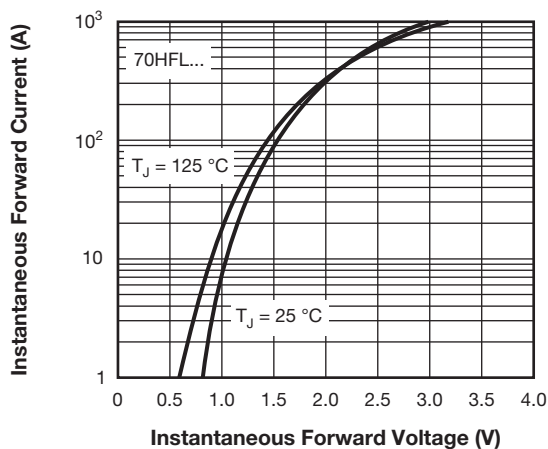


Fig. 12 - Maximum Forward Voltage vs. Forward Current, 70HFL Series

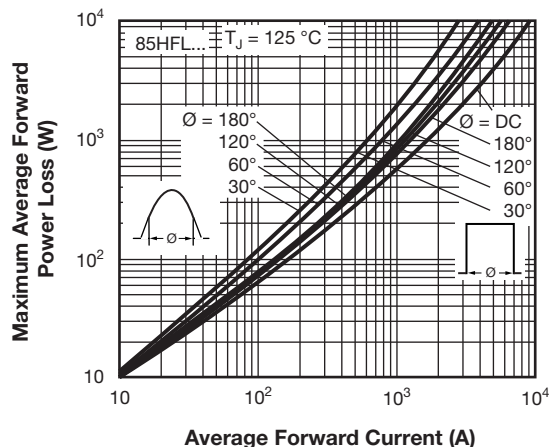


Fig. 10 - Maximum High Level Forward Power Loss vs. Average Forward Current, 85HFL Series

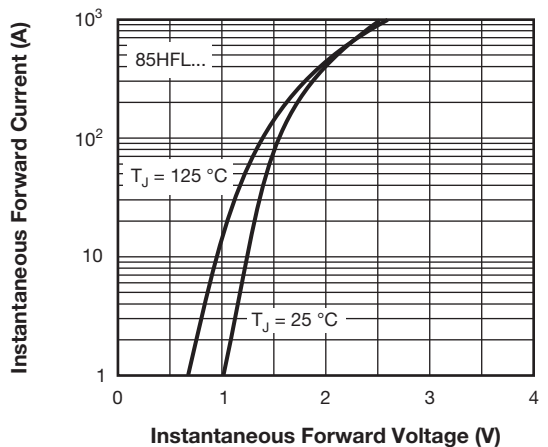


Fig. 13 - Maximum Forward Voltage vs. Forward Current, 85HFL Series

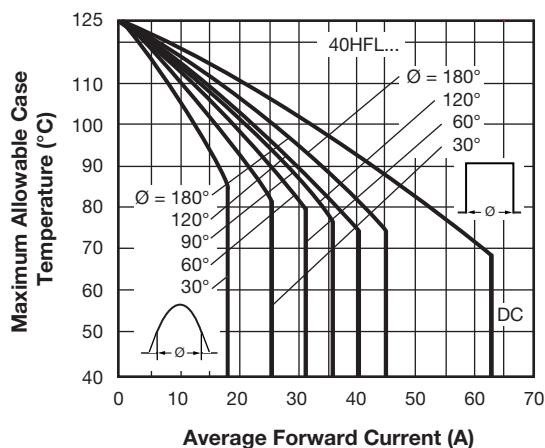


Fig. 14 - Average Forward Current vs. Maximum Allowable Case Temperature, 40HFL Series

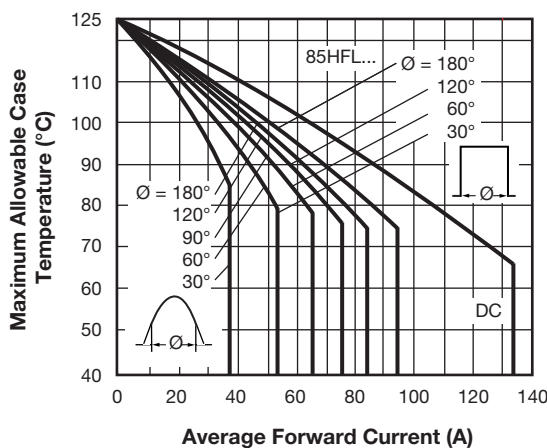


Fig. 16 - Average Forward Current vs. Maximum Allowable Case Temperature, 85HFL Series

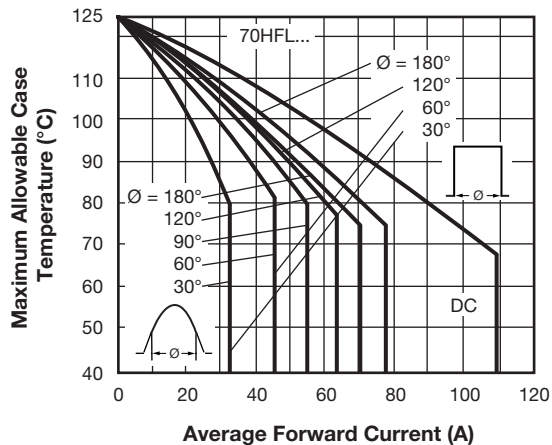


Fig. 15 - Average Forward Current vs. Maximum Allowable Case Temperature, 70HFL Series

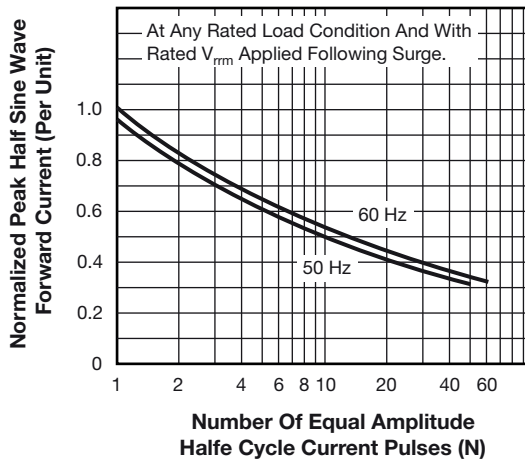


Fig. 17 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, All Series

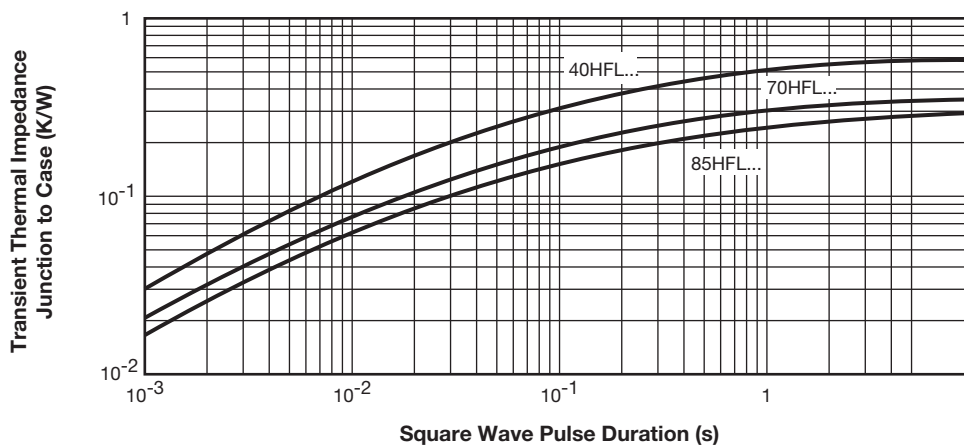


Fig. 18 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration, All Series

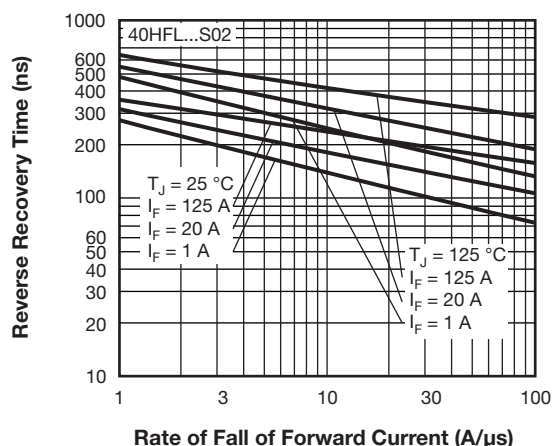


Fig. 19 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S02 Series

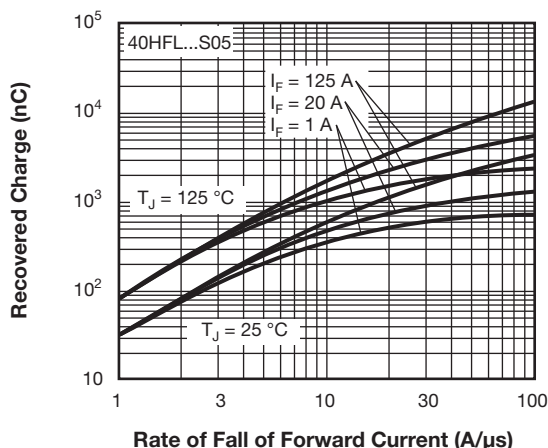


Fig. 22 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 40HFL...S05 Series

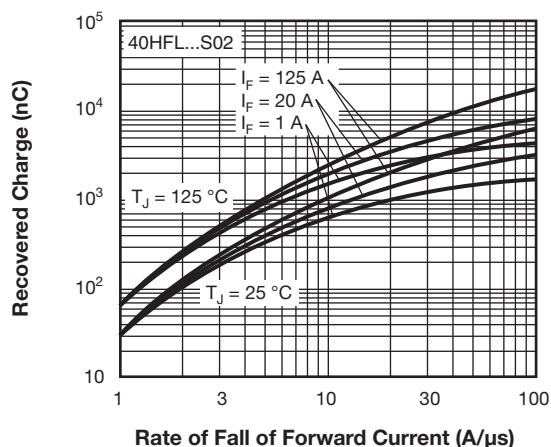


Fig. 20 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 40HFL...S02 Series

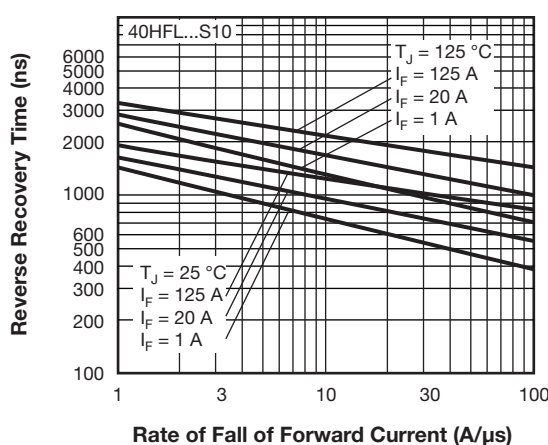


Fig. 23 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...Series

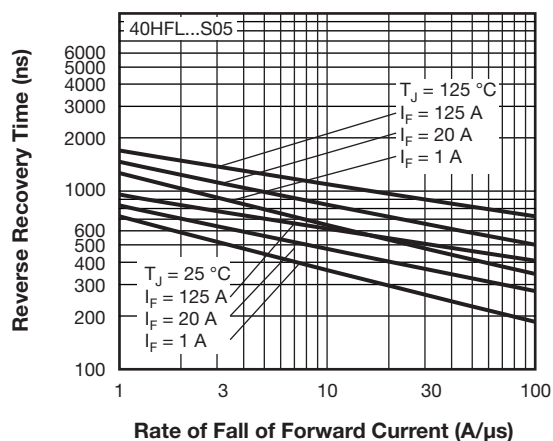


Fig. 21 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S05 Series

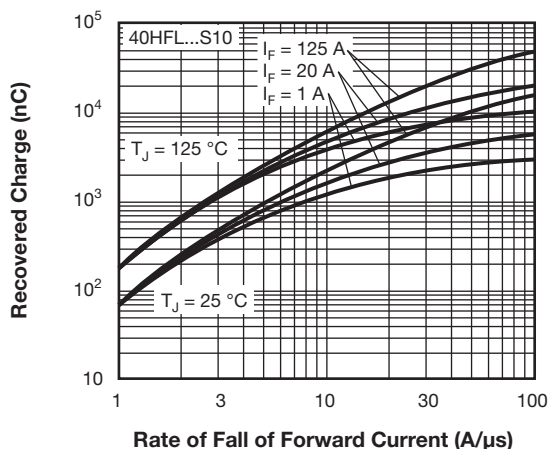


Fig. 24 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 40HFL...Series

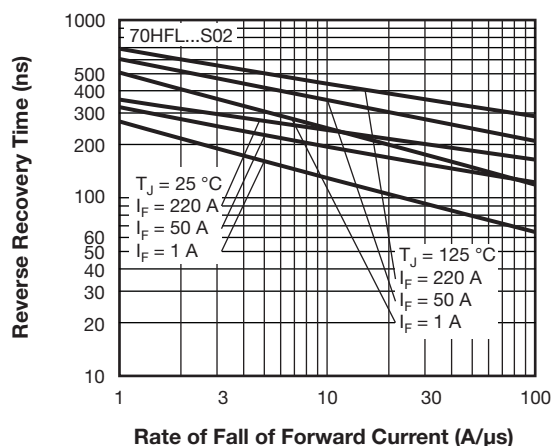


Fig. 25 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S02 Series

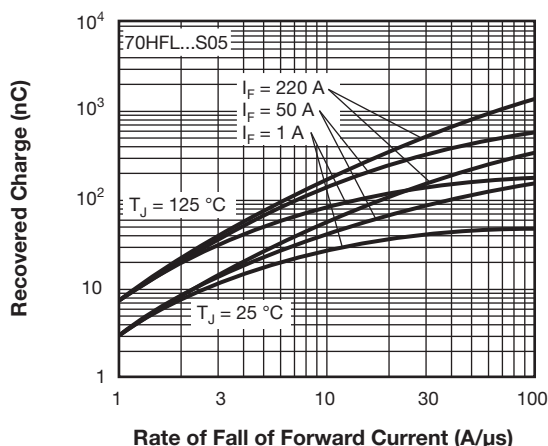


Fig. 28 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S05 Series

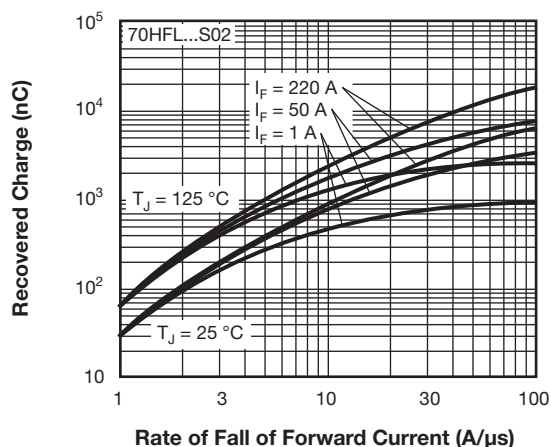


Fig. 26 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S02 Series

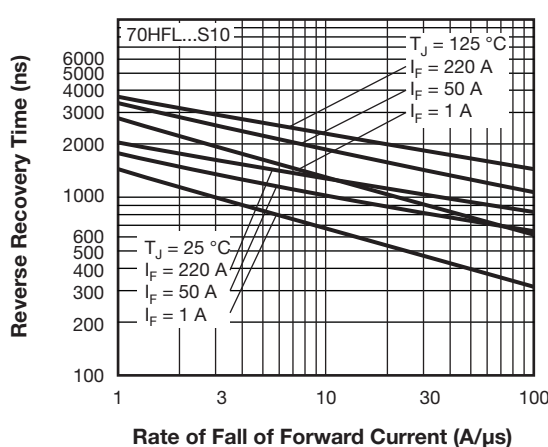


Fig. 29 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL... Series

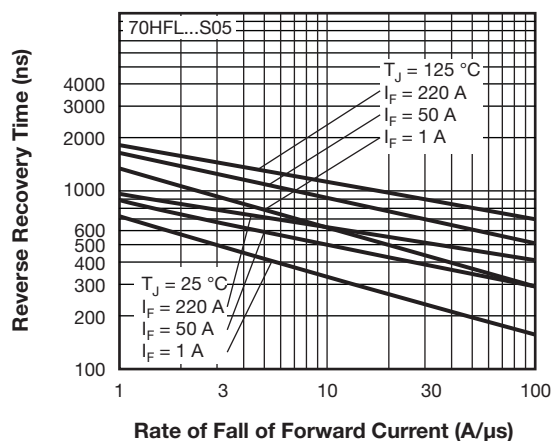


Fig. 27 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S05 Series

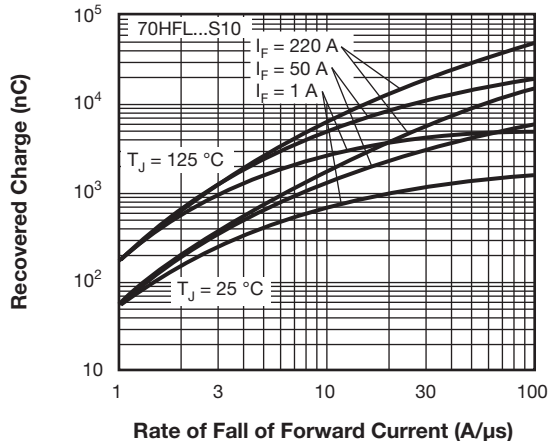
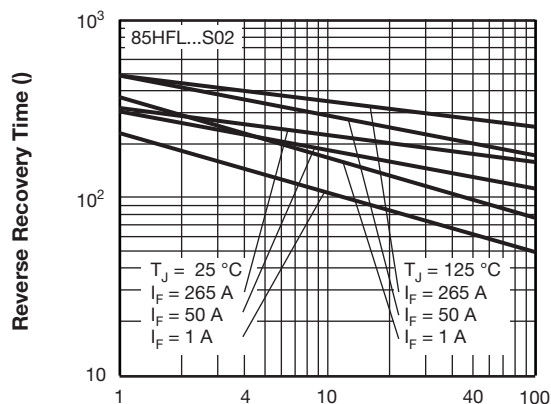
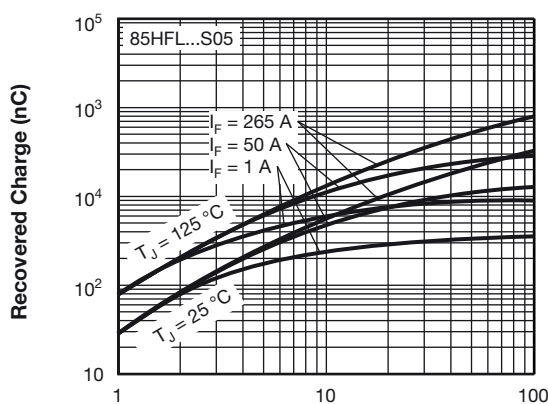


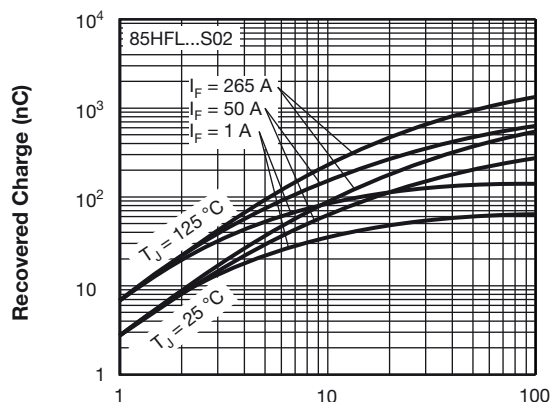
Fig. 30 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL... Series



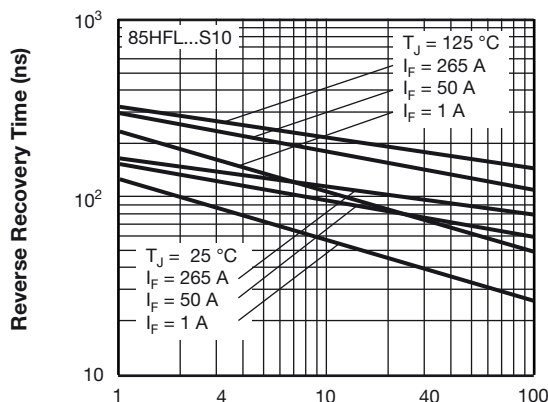
Rate of Fall of Forward Current (A/μs)
Fig. 31 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL...S02 Series



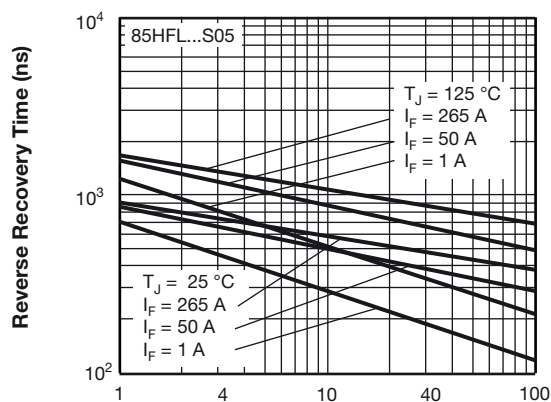
Rate of Fall of Forward Current (A/μs)
Fig. 34 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL...S05 Series



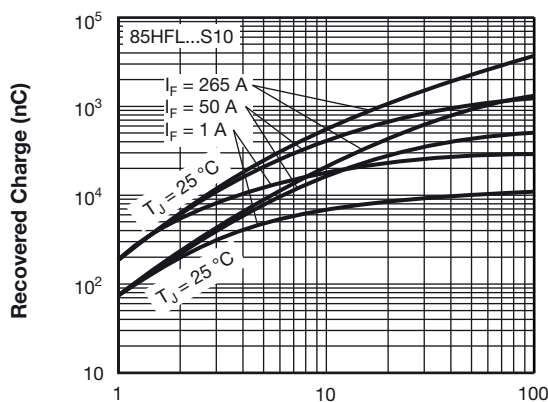
Rate of Fall of Forward Current (A/μs)
Fig. 32 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL...S02 Series



Rate of Fall of Forward Current (A/μs)
Fig. 35 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL... Series



Rate of Fall of Forward Current (A/μs)
Fig. 33 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL...S05 Series



Rate of Fall of Forward Current (A/μs)
Fig. 36 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL... Series

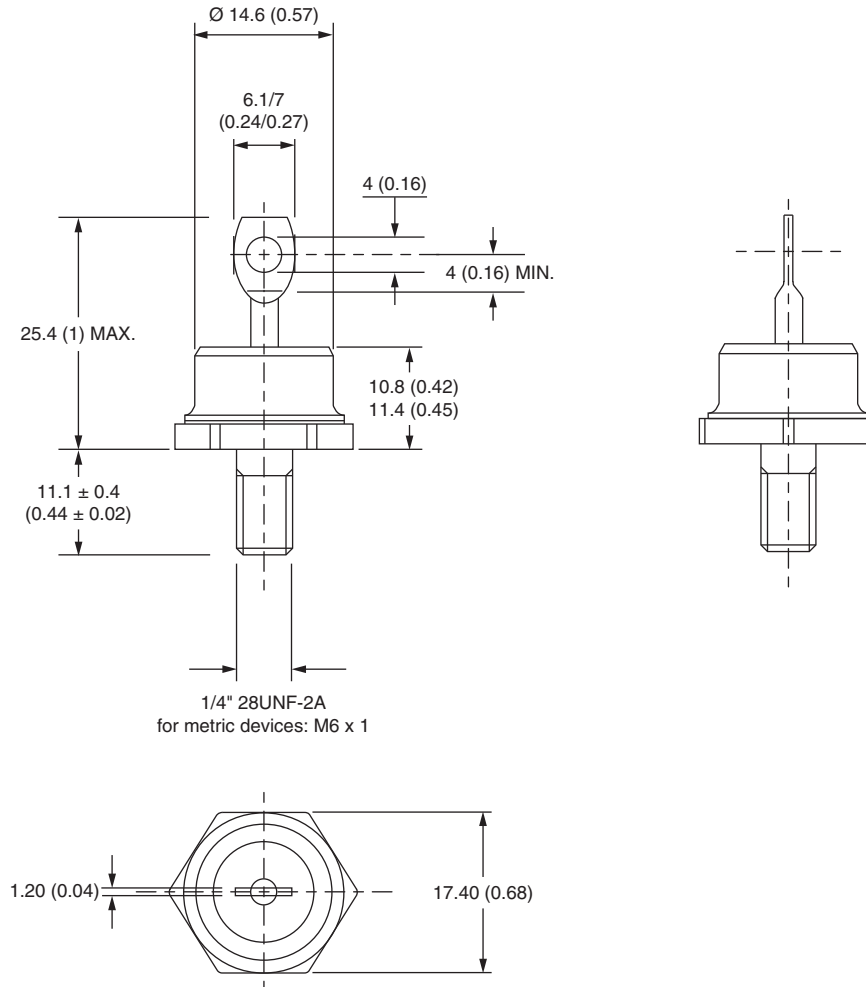
LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95312

DO-203AB (DO-5) for 40HFL, 70HFL and 85HFL

DIMENSIONS FOR 40HFL/70HFL in millimeters (inches)



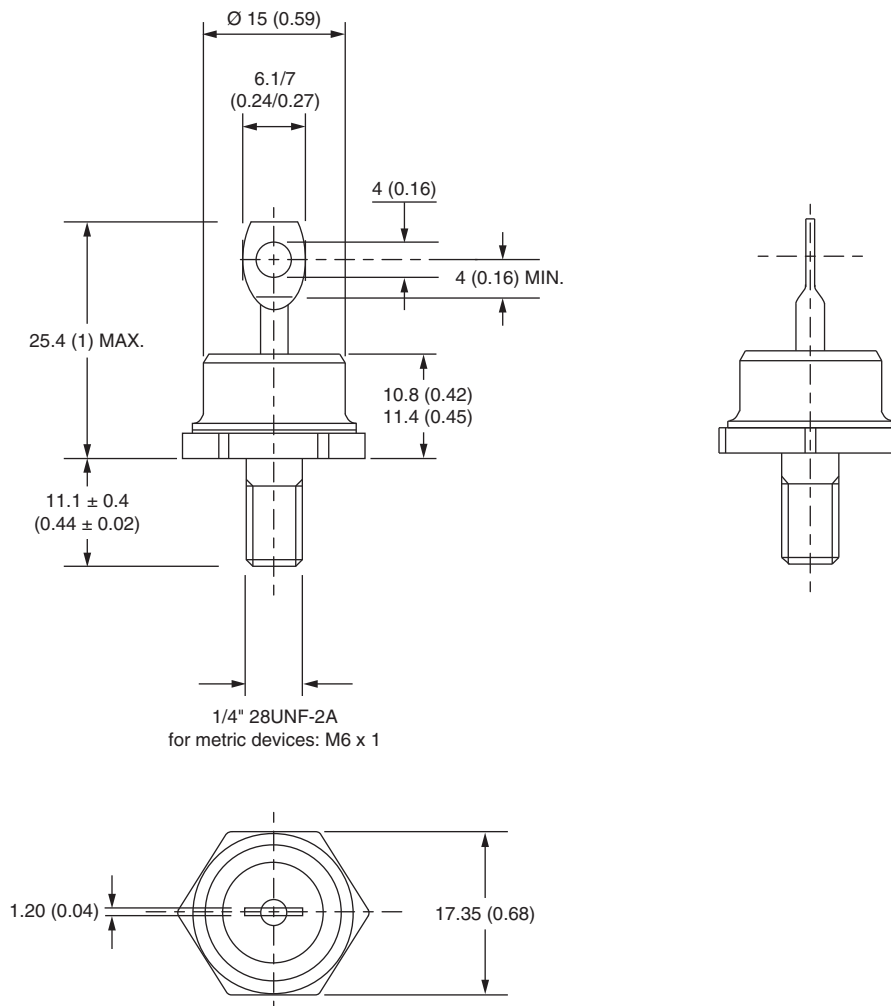
Outline Dimensions

Vishay Semiconductors

DO-203AB (DO-5) for
40HFL, 70HFL and 85HFL



DIMENSIONS FOR 85HFL in millimeters (inches)





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<http://moschip.ru/get-element>

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

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